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SPECIAL ISSUE ON

FET STRUCTURES AND THEIR CIRCUIT APPLICATIONS

Recent advances in GaAs compound semiconductor materials and improved processing technologies have resulted in several novel FET structures. Some of these structures are being extensively used in hybrid and monolithic integrated circuits at microwave and millimeter-wave frequencies. Others have been precluded from being used, mainly due to lack of awareness and insufficient design information.

MTT-S Technical Committees MTT-6, on Microwave and Millimeter-Wave Integrated Circuits, is sponsoring a Special Issue on FET Structures and Their Circuit Applications, to be published in September 1989. The objective is to present different FET structures, their circuit modeling, state-of-the-art results, and future trends. Topics of particular interest include, but are not limited to, the following areas:

- Active three-terminal devices, simulation, modeling, and circuit applications
- Additional applications (for example, mixers, oscillators, switches, multipliers) of three-terminal active devices such as MESFET's, MOSFET's, HEMT's, pseudomorphic MODFET's, HBT's and PBT's
- Device simulation and modeling
- Computer-aided design of hybrid and monolithic integrated circuits at microwave and millimeter-wave frequencies
- Novel device structures and innovative circuit concepts
- Low-noise and high-power applications
- Other related topics in state-of-the-art solid-state circuits

Mr. Jitendra Goel of TRW, Electronic Systems Group, will be Guest Editor of this Special Issue. Prospective authors are requested to submit five copies of the manuscript describing original work in the above areas by December 15, 1988, to:

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